

*PROCEEDINGS OF*  
*THE KAZUSA AKADEMIA PARK FORUM ON*  
*THE SCIENCE AND TECHNOLOGY OF SILICON MATERIALS '99*

*Editor : K. Sumino*

*November 24-26, 1999*

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*Organizing Committee of*  
*Silicon Materials Science and Technology Forum*

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The Science and Technology of Materials '99*

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## Preface

*The silicon materials technology makes progress most efficiently on the basis of the advance in the silicon materials science. Under such an idea Forums on the Science and Tehcnology of Silicon Materials have been organized at Kazusa Akademia Park, a scenic site in Chiba Prefecture, with purposes 1) to promote interactions between basic and applied researches related to the production of high quality silicon crystals and the development of advanced silicon processing, 2) to systematize the knowledge accumulated at industries and seek the seeds of basic research, 3) to discuss the way to solve the technical problems at the moment, and also 4) to offer instructive lectures on the science and technology of advanced silicon materials to beginners.*

*The Forum of 1999 follows the first one held on November 12-14, 1997. While the first Forum covered a very wide range of topics in the sicence and technology of silicon materials, the second Forum focuses on a rather limited number of subjects which are the most important issues of the modern silicon materials technology. It is intended to deepen the knowledge for such important issues rather than to survey the wide range of topics. The subjects taken up concern grown-in defects, precipitation of oxygen, and gettering of impurities. All of these subjects are closely related to each other and constitute the bases for other subjects. The very details of these issues are discussed.*

*The Forum '99 consists of twenty-four lecture-type presentations by experts living in Japan. As was in Forum '97, all the participants stay at the same hotel in the Park on November 24-26, 1999, and have an ample time for discussion.*

*We believe that these Forum Proceedings are the milestone in the science and technology of silicon materials at the end of the 1990s.*

November, 1999

Koji Sumino  
Forum Chairman

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